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TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD

BASED ON TYPE BUY25CS54A-01

ESCC Detail Specification No. 5205/027

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DCR No.	CHANGE DESCRIPTION

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1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

(a) ESCC Generic Specification No. 5000
(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices
(c) MIL-STD-883, Test Method Standard Microelectronics

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520502701R

- Detail Specification Reference: 5205027
- Component Type Variant Number: 01
- Total Dose Radiation Level Letter: R (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case (Note 1)	Weight max (g)	Total Dose Radiation Level Letter (Note 2)
01	BUY25CS54A-01	SMD2	3.3	R [100kRAD(Si)]

NOTES:

1. See Physical Dimensions and Terminal Identification.
2. Total dose radiation level letters are defined in ESCC Basic Specification No. 22900. If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

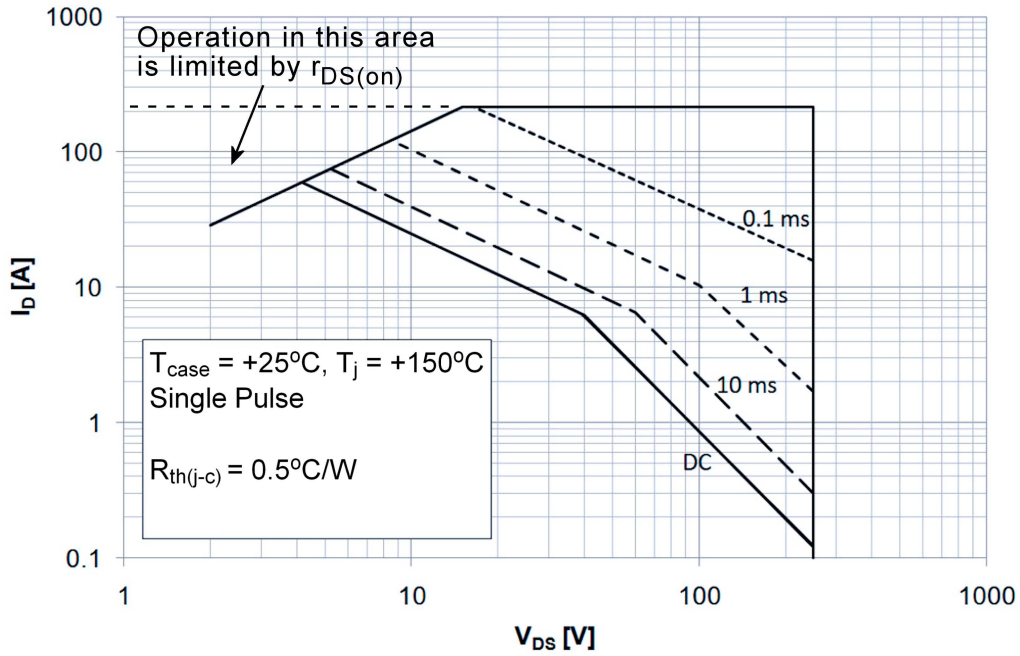
The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Drain-Source Voltage	V_{DS}	250	V	Note 1
Gate-Source Voltage	V_{GS}	±20	V	
Drain Current (Continuous)	I_{DS}	54	A	At T_{case} ≤+25°C Notes 1, 2, 3
Drain Current (Continuous)	I_{DS}	34	A	At T_{case} =+100°C Notes 2, 3
Drain Current (Pulsed)	I_{DM}	214	Apk	At T_{case} ≤+25°C Notes 1, 2,
Power Dissipation	P_{tot}	250	W	Note 4
Avalanche Energy (Single Pulse)	E_{AS}	380	mJ	
Operating Temperature Range	T_{op}	-55 to +150	°C	T_{amb}
Storage Temperature Range	T_{stg}	-55 to +150	°C	
Junction Temperature	T_j	+150	°C	
Soldering Temperature	T_{sol}	+250	°C	Note 5
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	0.5	°C/W	

NOTES:

1. Safe Operating Area applies as follows:



2. T_{case} is measured on the PCB at the soldering point to the Drain terminal.
3. For T_{case} >+25°C, derate as follows:

$$I_{DS} = \sqrt{\frac{T_{jmax} - T_{case}}{(R_{th(j-c)}) \times (r_{DS(on)} \text{ at } T_{jmax})}}$$

Where $r_{DS(on)}$ at T_{jmax} = 86mΩ

4. For T_{case} > +25°C, derate linearly to 0W at T_{case} = +150°C.
5. Duration 10 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

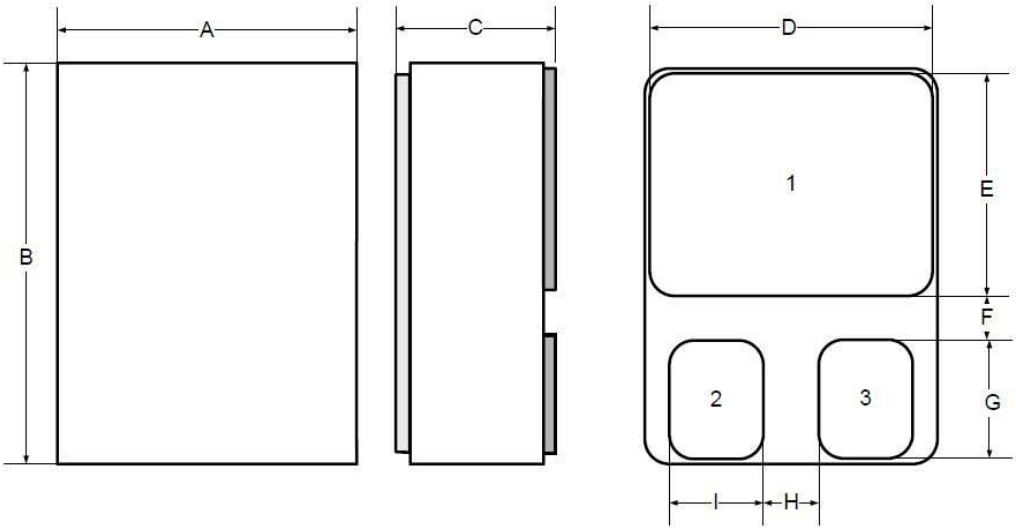
1.6 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a Minimum Critical Path Failure Voltage of 1000V.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 Leadless Chip Carrier Package (SMD2) - 3 Terminals



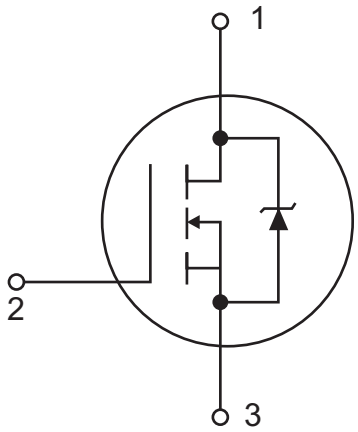
Symbols	Dimensions mm	
	Min	Max
A	13.14	13.54
B	17.3	17.75
C	-	3.75
D	11.05	11.3
E	11.94	12.19
F	0.89	-
G	3.86	4.11
H	1.27	-
I	3.43	3.68

NOTES:

1. Terminal identification: terminal 1 = Drain, terminal 2 = Gate, terminal 3 = Source.

1.8 FUNCTIONAL DIAGRAM

Terminal 1: Drain
Terminal 2: Gate
Terminal 3: Source



NOTES:
1. The case is not connected to any terminal.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case
The case shall be hermetically sealed and have a ceramic/metal body.
b) Terminals
The terminal material and finish shall be Q14 in accordance with the requirements of ESCC Basic Specification No. 23500.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviations from Screening Tests - Chart F3

(a) Verification of Safe Operating Area: The Safe Operating Area shall be verified by performing the Thermal Impedance ($Z_{th(j-s)}$) ΔV_{SD} test specified in Room Temperature Electrical Measurements.

(b) Particle Impact Noise Detection may be performed at any point after Temperature Cycling, prior to Seal.
(c) Power Burn-in: A high temperature steady-state gate bias test (HTGB) shall be performed instead

of Power Burn-in.

2.1.1.2 Deviations from Qualification and Periodic Testes - Chart F4

(a) Terminal Strength is not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

(a) The ESCC qualified components symbol (for ESCC qualified components only).
(b) The ESCC Component Number.
(c) Traceability information.

2.3 WAFER LOT ACCEPTANCE

A SEM inspection shall be performed as specified in the ESCC Generic Specification.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures. Consolidated notes are given after the tables.

2.4.1 Room Temperature Electrical Measurements

Unless otherwise specified, the measurements shall be performed at T_{amb}=+25 ±3°C.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	3407	V_{GS}=0V I_D=0.25mA Bias condition C	250	-	V
Gate-to-Source Threshold Voltage	$V_{GS(th)}$	3403	$V_{DS}\geq V_{GS}$ I_D=1mA	2	4	V
Gate-to-Source Leakage Current	I_{GSS}	3411	V_{GS}=±20V V_{DS}=0V Bias condition C	-100	+100	nA
Drain Current	I_{DSS}	3413	V_{GS}=0V V_{DS}=200V Bias condition C	-	25	µA
Static Drain-to-Source On Resistance	$r_{DS(on)}$	3421	V_{GS}=10V I_D=34A Note 1	-	30	mΩ

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Source-to-Drain Diode Forward Voltage	V_{SD}	4011	V_{GS}=0V I_{SD}=54A Note 1	-	1.2	V
Thermal Impedance,	$Z_{th(j-c)}$	3161	Note 2	-	0.24	^{o}C/W
Turn-on Delay Time	$t_{d(on)}$	3472	V_{GS}=10 V, R_G=4.7Ω V_{DS}=125V, I_D=34A Note 3	-	80	ns
Rise Time	t_r	3472	V_{GS}=10 V, R_G=4.7Ω V_{DS}=125V, I_D=34A Note 3	-	80	ns
Turn-off Delay Time	$t_{d(off)}$	3472	V_{GS}=10 V, R_G=4.7Ω V_{DS}=125V, I_D=34A Note 3	-	130	ns
Fall Time	t_f	3472	V_{GS}=10 V, R_G=4.7Ω V_{DS}=125V, I_D=34A Note 3	-	80	ns
Reverse Recovery Time	t_{rr}	3473	V_{DD}≤50V, di/dt=100A/µs I_{SD}=54A Note 3	-	700	ns
Input Capacitance	C_{iss}	3431	V_{GS}=0V, V_{DS}=100V f=1MHz Note 3	9	14	nF
Output Capacitance	C_{oss}	3453	V_{GS}=0V, V_{DS}=100V f=1MHz Note 3	600	1000	pF
Reverse Transfer Capacitance	C_{rss}	3433	V_{GS}=0V, V_{DS}=100V f=1MHz Note 3	5	30	pF
Total Gate Charge	Q_g	3471	V_{GS}=10V, V_{DS}=125V, I_D=54A Note 3	-	180	nC
Gate-to-Source Charge	Q_{gs}	3471	V_{GS}=10V, V_{DS}=125V, I_D=54A Note 3	-	55	nC
Gate-to-Drain Charge	Q_{gd}	3471	V_{GS}=10V, V_{DS}=125V, I_D=54A Note 3	-	55	nC

2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 4	Limits		Units
				Min	Max	
Gate-to-Source Threshold Voltage	$V_{GS(th)}$	3403	T_{amb}=+125(+0-5)^{o}C $V_{DS} \geq V_{GS}$ I_D=1mA	1.5	-	V
			T_{amb}=-55(+5-0)^{o}C $V_{DS} \geq V_{GS}$ I_D=1mA	-	5	V
Gate-to-Source Leakage Current	I_{GSS}	3411	T_{amb}=+125(+0-5)^{o}C V_{GS}=±20V, V_{DS}=0V Bias condition C	-200	+200	nA
Drain Current	I_{DSS}	3413	T_{amb}=+125(+0-5)^{o}C V_{GS}=0V V_{DS}=200V Bias condition C	-	250	µA
Static Drain-to-Source On Resistance	$r_{DS(on)}$	3421	T_{amb}=+125(+0-5)^{o}C V_{GS}=10V I_D=34A Note 1	-	70	mΩ

2.4.3 Notes to Room, High and Low Temperatures Electrical Measurements

1. Pulsed measurement: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
2. The $Z_{th(j-c)}$ limit is guaranteed by performing a ΔV_{SD} (go-no-go) test. The following test conditions and limits shall apply:
   - V_{DS} = 20V
   - t_M < 75µs
   - I_M = 10mA
   - t_H = 25ms
   - I_H = 5.4A
   - V_{SD} = 40mV minimum, 60mV maximum
3. Read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
4. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb}=+25 ±3^{o}C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Gate-to-Source Threshold Voltage	$V_{GS(th)}$	±20%	2	4	V
Gate-to-Source Leakage Current	I_{GSS}	±20 or (1) ±100%	-100	+100	nA
Drain Current	I_{DSS}	±10 or (1) ±100%	-	25	µA
Static Drain-to-Source On Resistance (Note 2)	$r_{DS(on)}$	±20% (3)	-	30	mΩ

NOTES:
1. Whichever is the greater.
2. Measured only prior to HTRB Burn-in and after HTGB Burn-in.
3. Referred to the measurement prior to HTRB Burn-in.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb}=+25 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Gate-to-Source Threshold Voltage	$V_{GS(th)}$	±20%	2	4	V
Gate-to-Source Leakage Current	I_{GSS}	±20 or (1) ±100%	-100	+100	nA
Drain Current	I_{DSS}	±10 or (1) ±100%	-	25	µA
Static Drain-to-Source On Resistance	$r_{DS(on)}$	±20%	-	30	mΩ

NOTES:
1. Whichever is greater.

2.7 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

HTRB Burn-in shall be performed in accordance with MIL-STD-750, Test Method 1042, Test Condition A with the following conditions:

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150(+0-5)	^{o}C
Drain-to-Source Voltage	V_{DS}	200 (Note 1)	V
Gate-to-Source Voltage	V_{GS}	0	V
Duration	t	240 minimum	hours

NOTES:

1. Voltage may be switched off during cool down.

2.8 HIGH TEMPERATURE STEADY-STATE GATE BIAS BURN-IN CONDITIONS

HTGB Burn-in shall be performed in accordance with MIL-STD-750, Test Method 1042, Test Condition B with the following conditions:

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150(+0-5)	^{o}C
Drain-to-Source Voltage	V_{DS}	0	V
Gate-to-Source Voltage	V_{GS}	16	V
Duration	t	48 minimum	hours

2.9 OPERATING LIFE CONDITIONS

Operating Life shall consist of High Temperature Reverse Bias in accordance with MIL-STD-750, Test Method 1042, Test Condition A, followed by High Temperature Steady-State Gate Bias in accordance with MIL-STD-750, Test Method 1042, Test Condition B. The test conditions are as follows:

High Temperature Reverse Bias Conditions

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150(+0-5)	^{o}C
Drain-to-Source Voltage	V_{DS}	200 (Note 1)	V
Gate-to-Source Voltage	V_{GS}	0	V
Duration	t	1000 minimum	Hours

High Temperature Steady-State Gate Bias Conditions

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150(+0-5)	^{o}C
Drain-to-Source Voltage	V_{DS}	0	V
Gate-to-Source Voltage	V_{GS}	16	V

Characteristics	Symbols	Test Conditions	Units
Duration	t	1000 minimum	hours

NOTES:

1. Voltage may be switched off during cool down.

2.10 TOTAL DOSE RADIATION TESTING

2.10.1 Bias Conditions and Total Dose Level for Total Dose Radiation Testing

The following bias condition shall be used during irradiation testing:

V_{GS} = +15V

V_{DS} = 0V

The total dose level applied shall be as specified in Component Type Variants herein or in the Purchase Order.

2.10.2 Electrical Measurements for Total Dose Radiation Testing

Prior to irradiation testing the devices shall have successfully met Room Temperature Electrical Measurements specified herein.

Unless otherwise stated the measurements shall be performed at T_{amb} = 25±3°C.

Unless otherwise specified the test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

Characteristics	Symbols	Limits			Units
		Drift Values (Δ)	Absolute		
			Min	Max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	±20%	250	-	V
Gate-to-Source Threshold Voltage	$V_{GS(th)}$	+10%, -50%	2	4	V
Gate-to-Source Leakage Current	I_{GSS}	±20	-100	+100	nA
Drain Current	I_{DSS}	–	-	25	µA
Static Drain-to-Source On Resistance Variants 01, 03: Variant 02:	$r_{DS(on)}$	±20%	-	30	mΩ
Source-to-Drain Diode Forward Voltage	V_{SD}	±10%	-	1.2	V

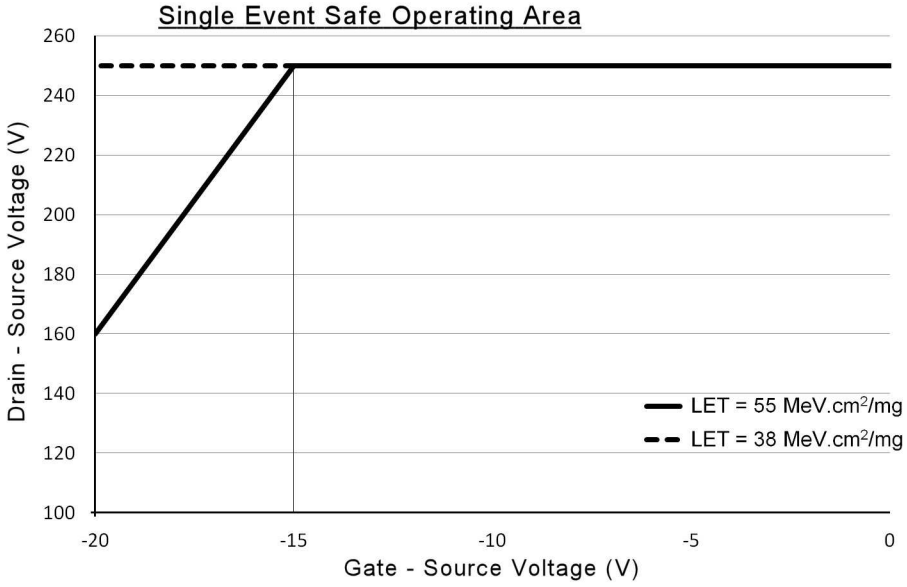
APPENDIX 'A'

AGREED DEVIATIONS FOR INFINEON TECHNOLOGIES (D)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Production Control (Chart F2)	The 3 component sample Dimension Check need only be performed once on each component package production lot.
Deviations from Screening Tests (Chart F3)	Temperature Cycling shall be performed in accordance with MIL-STD-883, Test Method 1010, Test Condition C, 20 cycles at maximum storage temperature rating specified in the Detail Specification.
	High and Low Temperatures Electrical Measurements may be performed at any point after High Temperature Steady-State Gate Bias Burn-in, prior to Seal, but shall still count towards Check for Lot Failure.
	Radiographic Inspection is not applicable.
	Seal, Fine Leak shall be performed in accordance with MIL-STD-883, Test Method 1014, Test Condition A1 or A2.
	Solderability is not applicable unless otherwise stipulated in the Purchase Order.
Deviations from Qualification and Periodic Tests (Chart F4)	Temperature Cycling shall be performed in accordance with MIL-STD-883, Test Method 1010, Test Condition C, 100 cycles at maximum storage temperature rating specified in the Detail Specification.
	Seal, Fine Leak shall be performed in accordance with MIL-STD-883, Test Method 1014, Test Condition A1 or A2.
Room Temperature Electrical Measurements	The read and record 32 component sample electrical measurements for characteristics $t_{d(on)}$, t_r, $t_{d(off)}$, t_f, t_{rr}, C_{iss}, C_{oss}, C_{rss}, Q_g, Q_{gs} and Q_{gd} need only be performed once on each wafer lot used to supply components to this specification. Any failure shall result in rejection of the wafer lot. The sample measurement may be performed at any time during production.
Marking	For the purposes of marking of the ESCC Component Number on the body of the component, the Variant Number may be marked as a single digit (e.g. 1 for Variant 01). Otherwise the full ESCC Component Number shall be used.

ADDITIONAL DATA - INFINEON TECHNOLOGIES (D)

(a) Derating for Space Application
These components are susceptible to Single Event Gate Rupture if operated in a space environment unless the following derating is applied:


Single Event Safe Operating Area
Drain - Source Voltage (V)
260
240
220
200
180
160
140
120
100
-20
-15
-10
-5
0
Gate - Source Voltage (V)
LET = 55 MeV.cm²/mg
LET = 38 MeV.cm²/mg